

Dual N-Channel 20 V MOSFET

PRODUCT SUMMARY

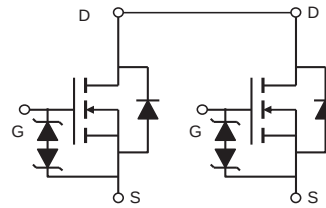
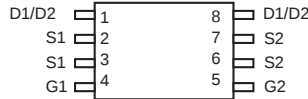
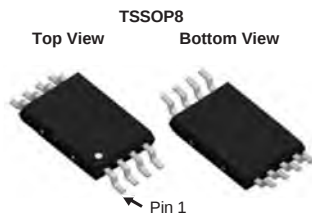
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
20	0.0048 at $V_{GS} = 4.5$ V	11 ^a	14.5
	0.0067 at $V_{GS} = 2.5$ V	9	

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC
- ESD Protected 2KV HBM



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$)	$T_C = 25\text{ }^{\circ}\text{C}$	I_D	11	A
	$T_C = 70\text{ }^{\circ}\text{C}$		9.9	
	$T_A = 25\text{ }^{\circ}\text{C}$		10.5 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		8.2 ^{b, c}	
Pulsed Drain Current (10 μs Pulse Width)		I_{DM}	30	
Source-Drain Current Diode Current	$T_C = 25\text{ }^{\circ}\text{C}$	I_S	2.7	
	$T_A = 25\text{ }^{\circ}\text{C}$		1.6 ^{b, c}	
Pulsed Source-Drain Current		I_{SM}	30	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	10	
Single Pulse Avalanche Energy		E_{AS}	10	
Maximum Power Dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	P_D	3.25	W
	$T_C = 70\text{ }^{\circ}\text{C}$		2.10	
	$T_A = 25\text{ }^{\circ}\text{C}$		2.0 ^{b, c}	
	$T_A = 70\text{ }^{\circ}\text{C}$		1.25 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	45	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Foot (Drain)	R_{thJF}	29	38	

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface mounted on 1" x 1" FR4 board.

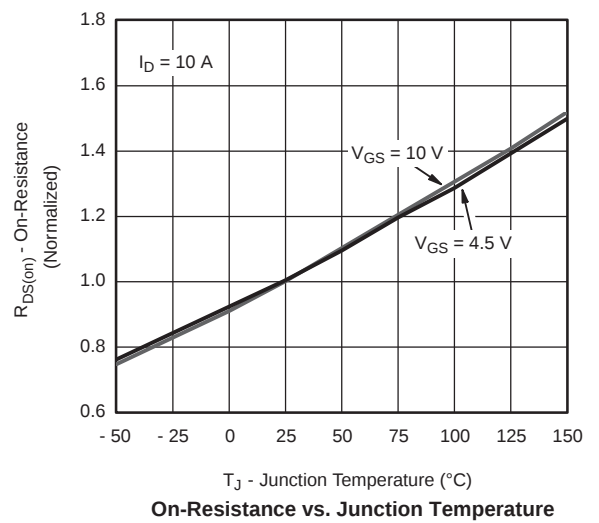
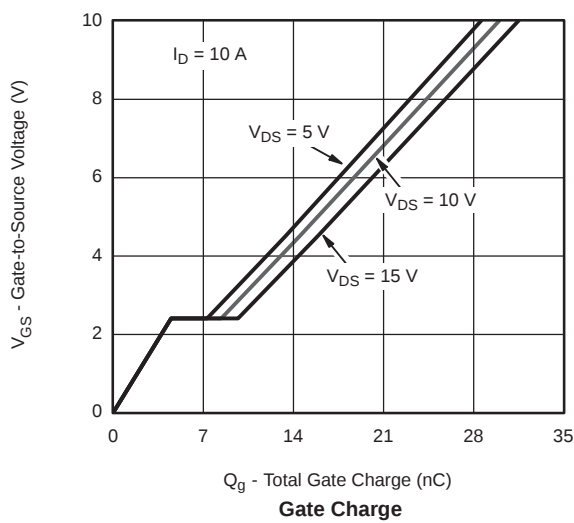
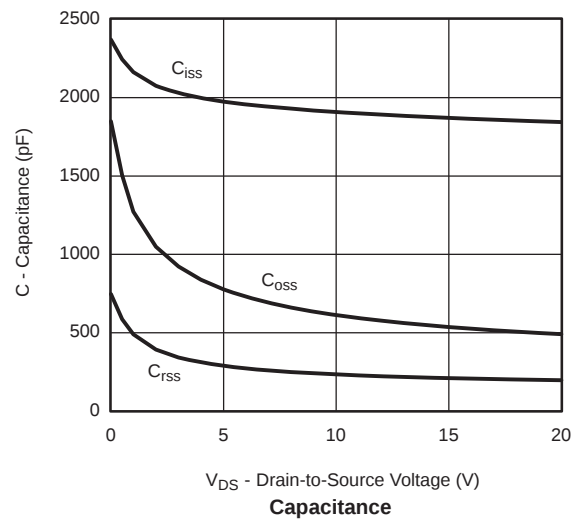
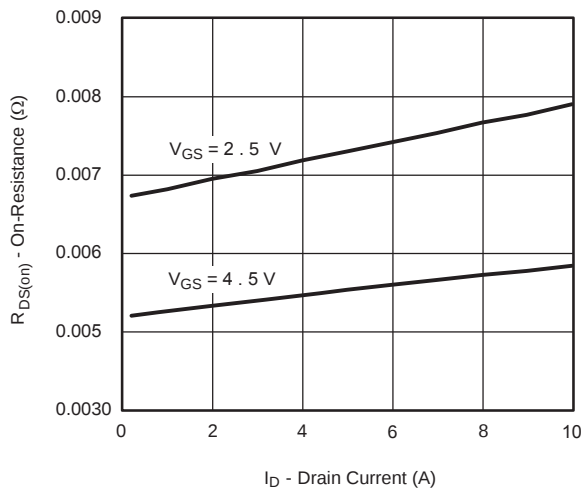
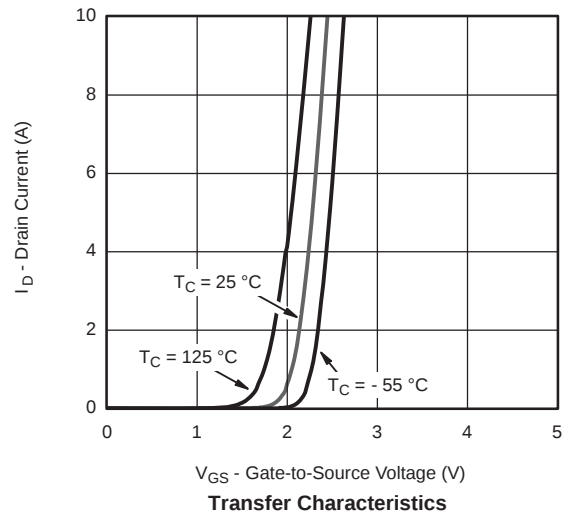
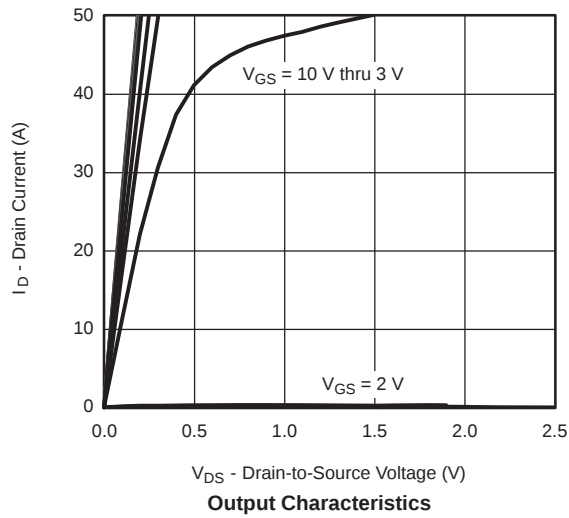
c. $t = 10$ s.

d. Maximum under steady state conditions is 120 $^\circ\text{C/W}$.

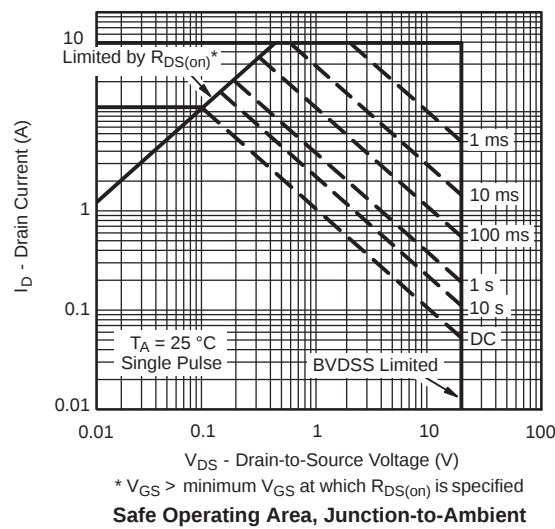
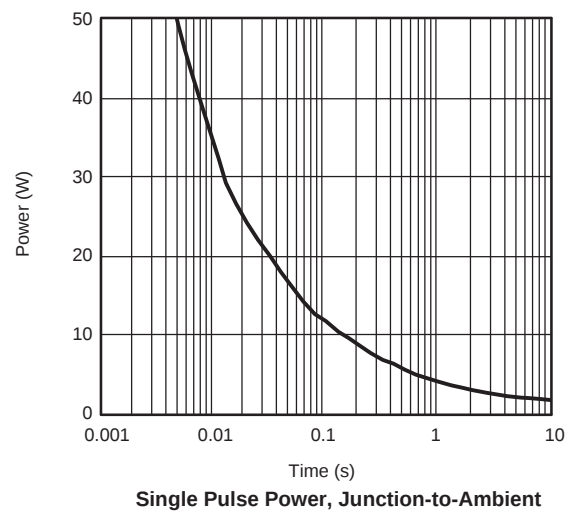
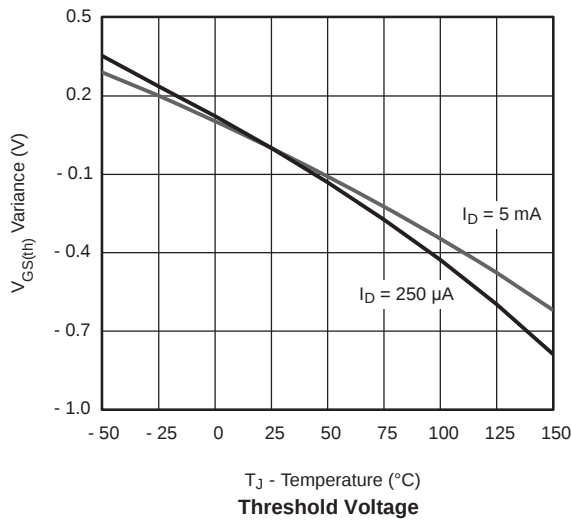
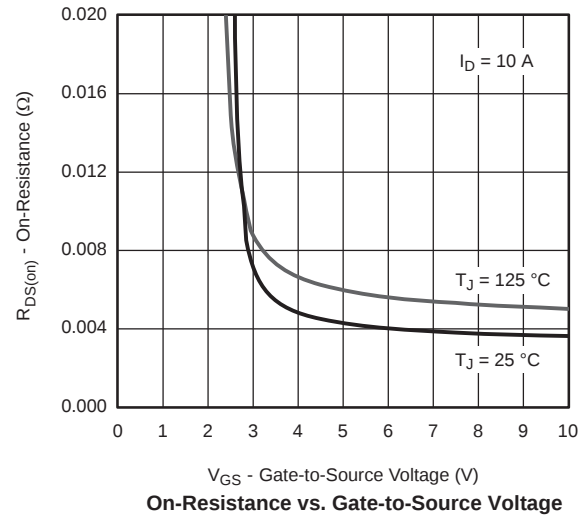
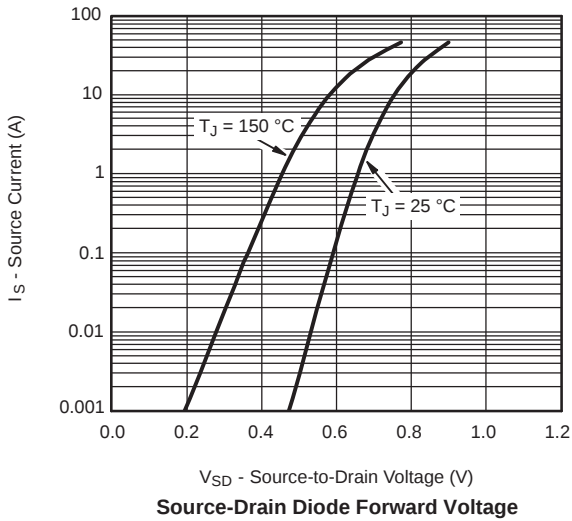
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	20			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		20		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J	I _D = 250 μA		- 5.8		
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.6		1.2	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			10	uA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	11			A
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 10 A		0.0048		Ω
		V _{GS} = 2.5 V, I _D = 8 A		0.0067		
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A		50		S
Dynamic ^a						
Input Capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V, I _D = 1 MHz		2110		pF
Output Capacitance	C _{oss}			926		
Reverse Transfer Capacitance	C _{rss}			235		
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 10 V, I _D = 10 A		30	45	nC
		V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 10 A		14.5	22	
Gate-Source Charge	Q _{gs}			4.5		
Gate-Drain Charge	Q _{gd}			3.9		
Gate Resistance	R _g	f = 1 MHz	0.4	1.4	2.8	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 1 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω		8	16	ns
Rise Time	t _r			15	30	
Turn-Off Delay Time	t _{d(off)}			24	45	
Fall Time	t _f			9	18	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 1 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω		18	35	
Rise Time	t _r			24	45	
Turn-Off Delay Time	t _{d(off)}			26	50	
Fall Time	t _f			13	26	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			2.7	A
Pulse Diode Forward Current ^a	I _{SM}				50	
Body Diode Voltage	V _{SD}	I _S = 3 A		0.70	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	N-Channel I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C		20	40	ns
Body Diode Reverse Recovery Charge	Q _{rr}			10	20	nC
Reverse Recovery Fall Time	t _a			11		nS
Reverse Recovery Rise Time	t _b			9		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

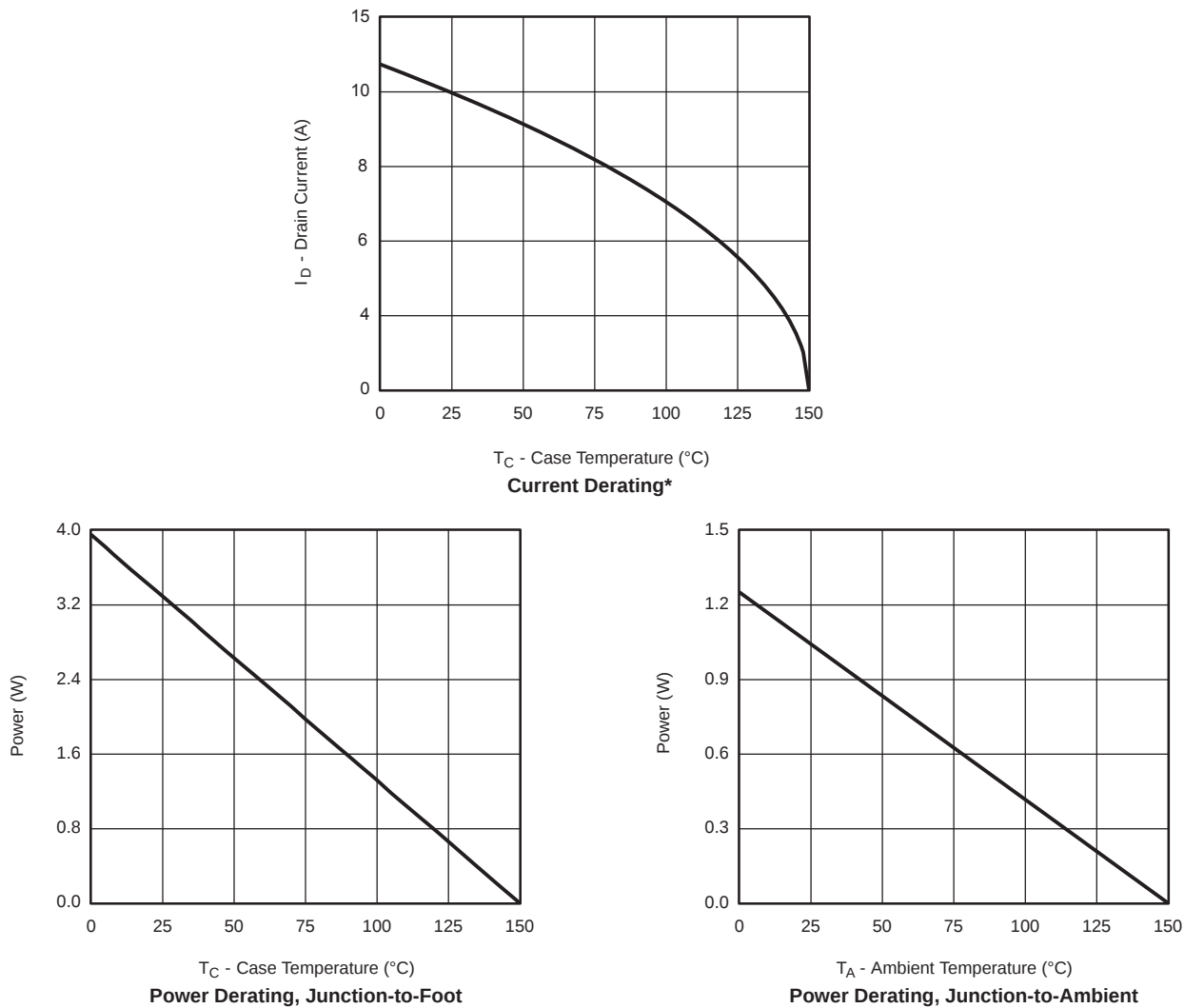
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



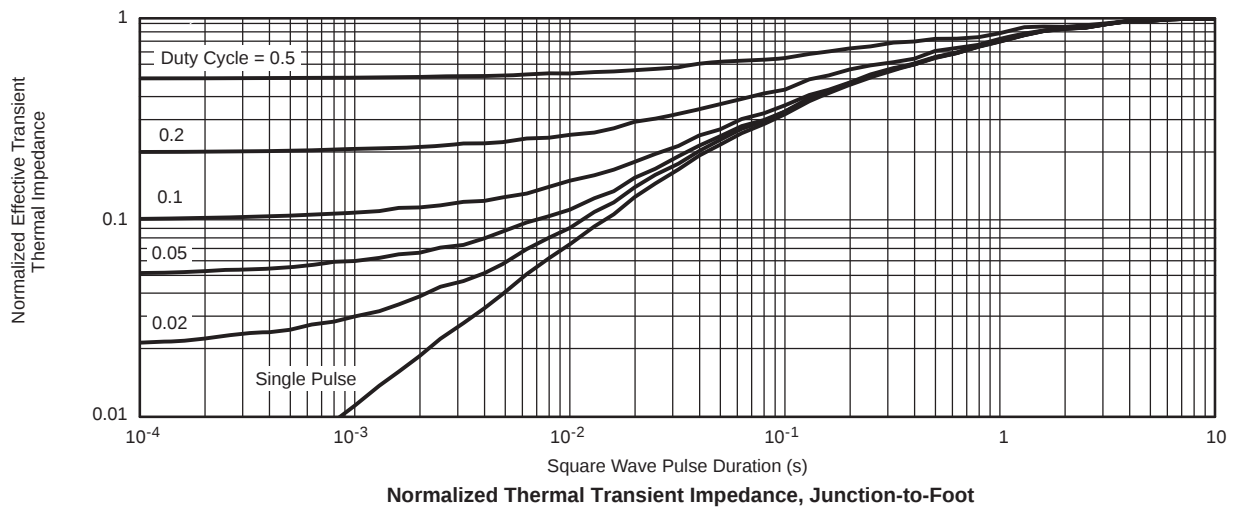
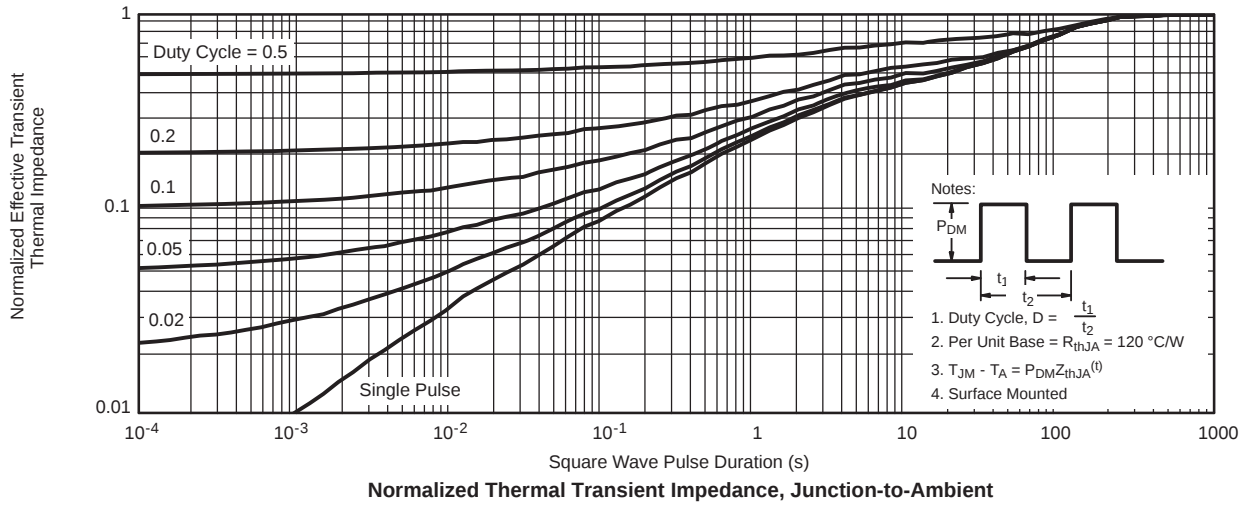
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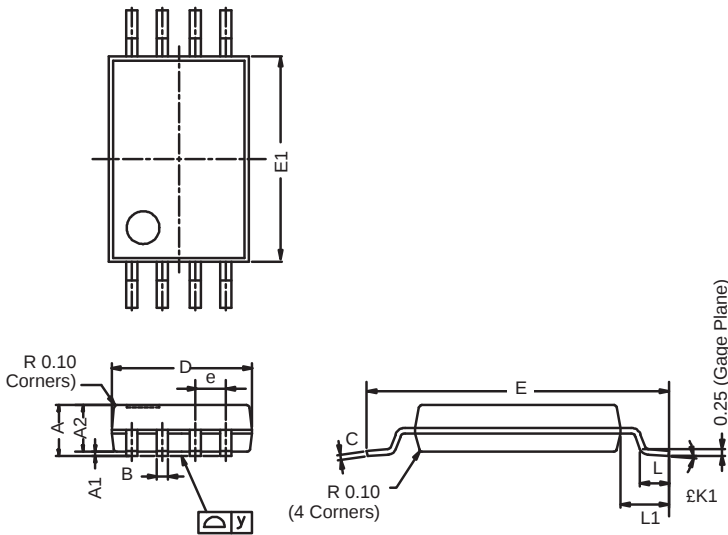
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* The power dissipation P_D is based on $T_{J(\text{max})} = 150\text{ }^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

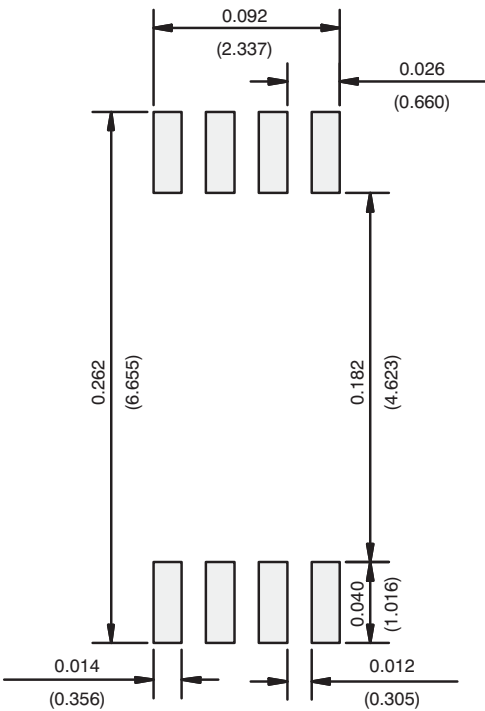
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


TSSOP: 8-LEAD
JEDEC Part Number: MO-153



Dim	MILLIMETERS		
	Min	Nom	Max
A	—	—	1.20
A ₁	0.05	0.10	0.15
A ₂	0.80	1.00	1.05
B	0.19	0.28	0.30
C	—	0.127	—
D	2.90	3.00	3.10
E	6.20	6.40	6.60
E ₁	4.30	4.40	4.50
e	—	0.65	—
L	0.45	0.60	0.75
L ₁	0.90	1.00	1.10
Y	—	—	0.10
£K1	0°	3°	6°
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844			

RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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